

Fig. 1A
(Prior Art)

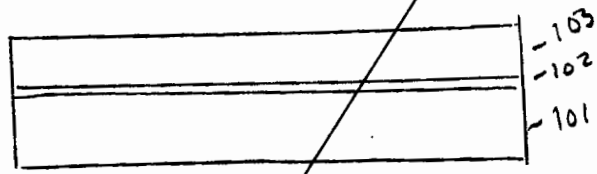


Fig. 1B
(Prior Art)

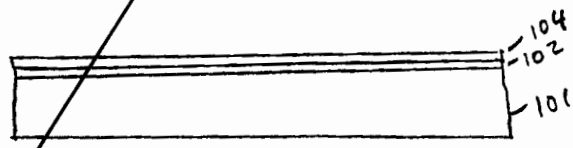


Fig. 1C
(Prior Art)

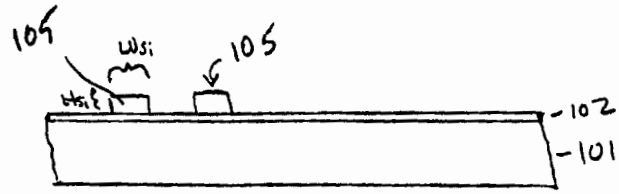


Fig. 1D
(Prior Art)

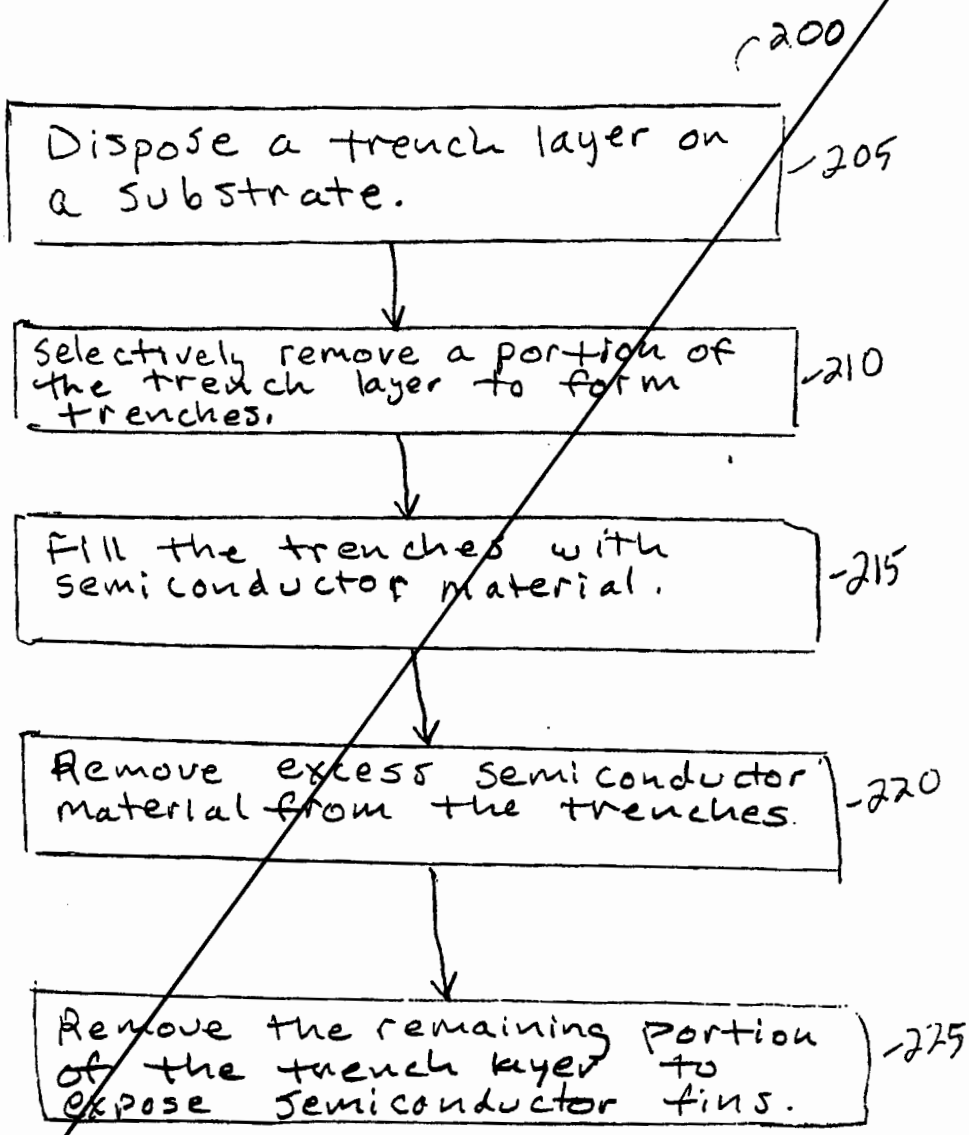

200
Dispose a trench layer on a substrate.
205
Selectively remove a portion of the trench layer to form trenches.
210
Fill the trenches with semiconductor material.
215
Remove excess semiconductor material from the trenches.
220
Remove the remaining portion of the trench layer to expose semiconductor fins.
225

Fig. 2

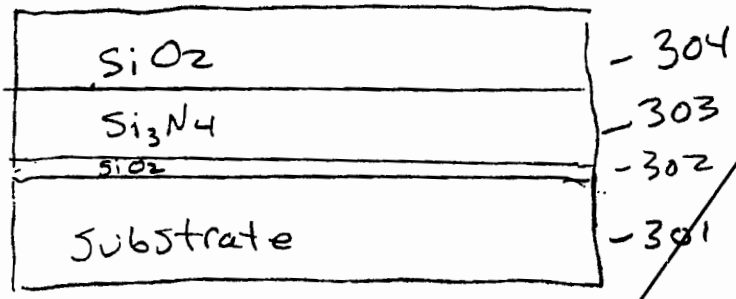


Fig. 3A

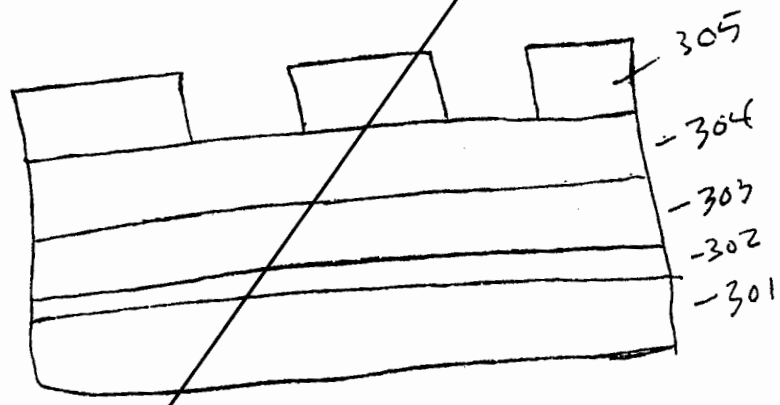


Fig 3B

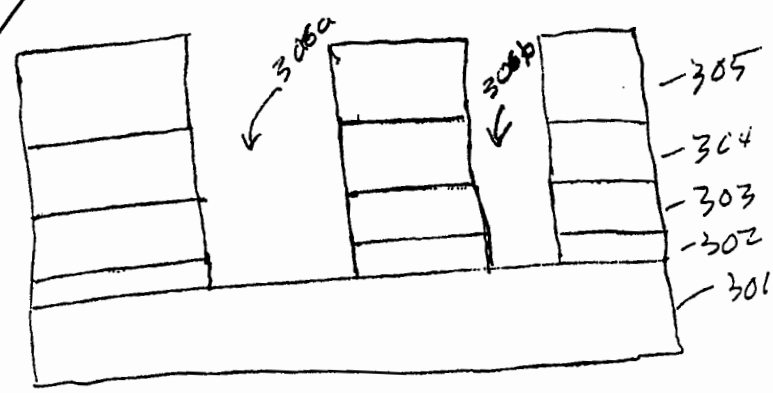


Fig. 3C

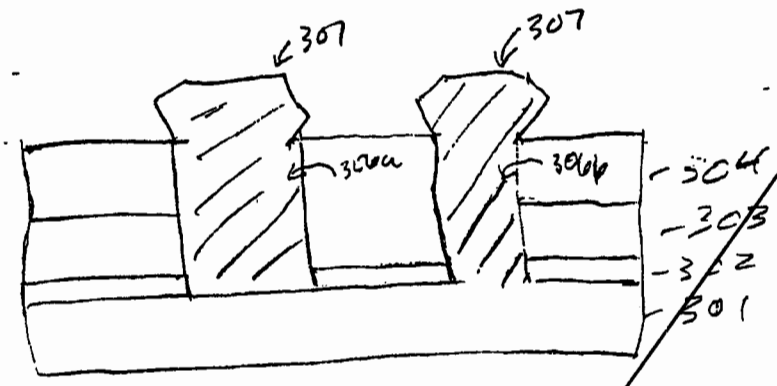


Fig. 3D

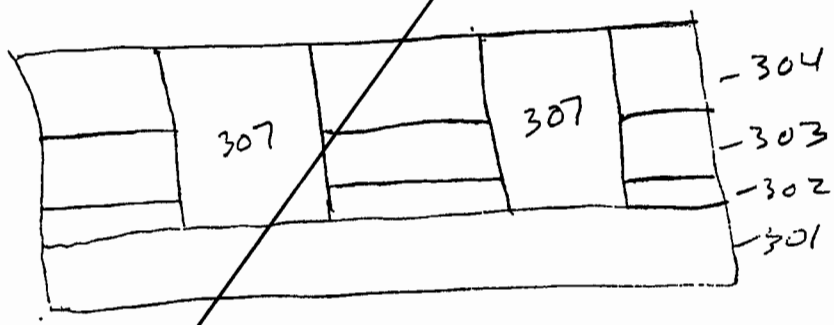


Fig. 3E

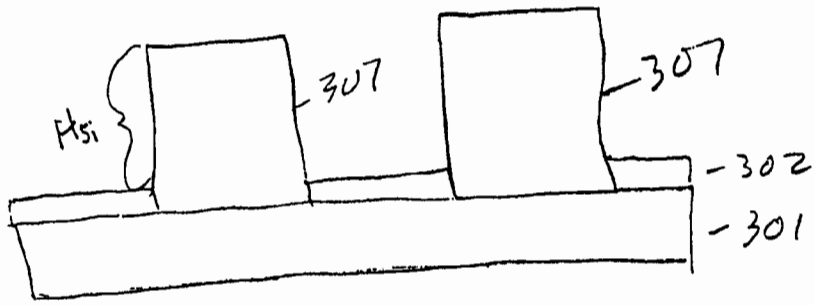


Fig. 3F

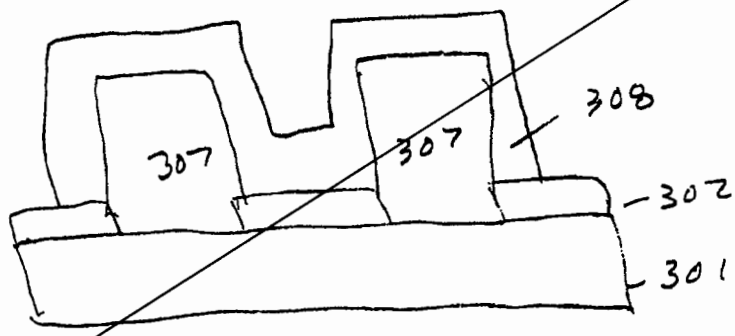


Fig. 3G

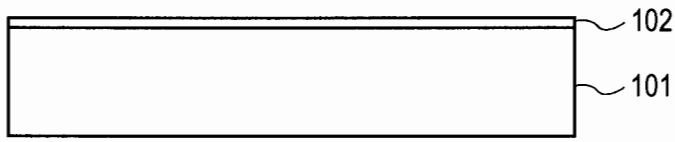


FIG. 1A
(PRIOR ART)

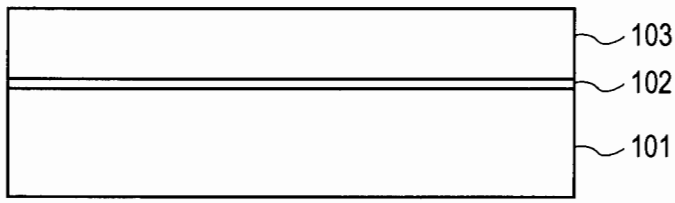


FIG. 1B
(PRIOR ART)

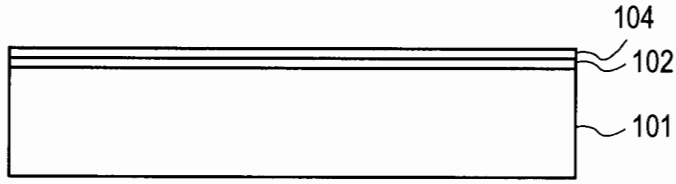


FIG. 1C
(PRIOR ART)

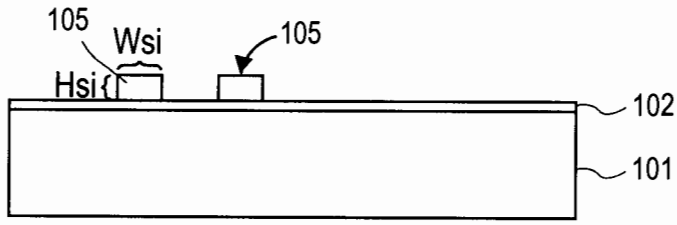


FIG. 1D
(PRIOR ART)

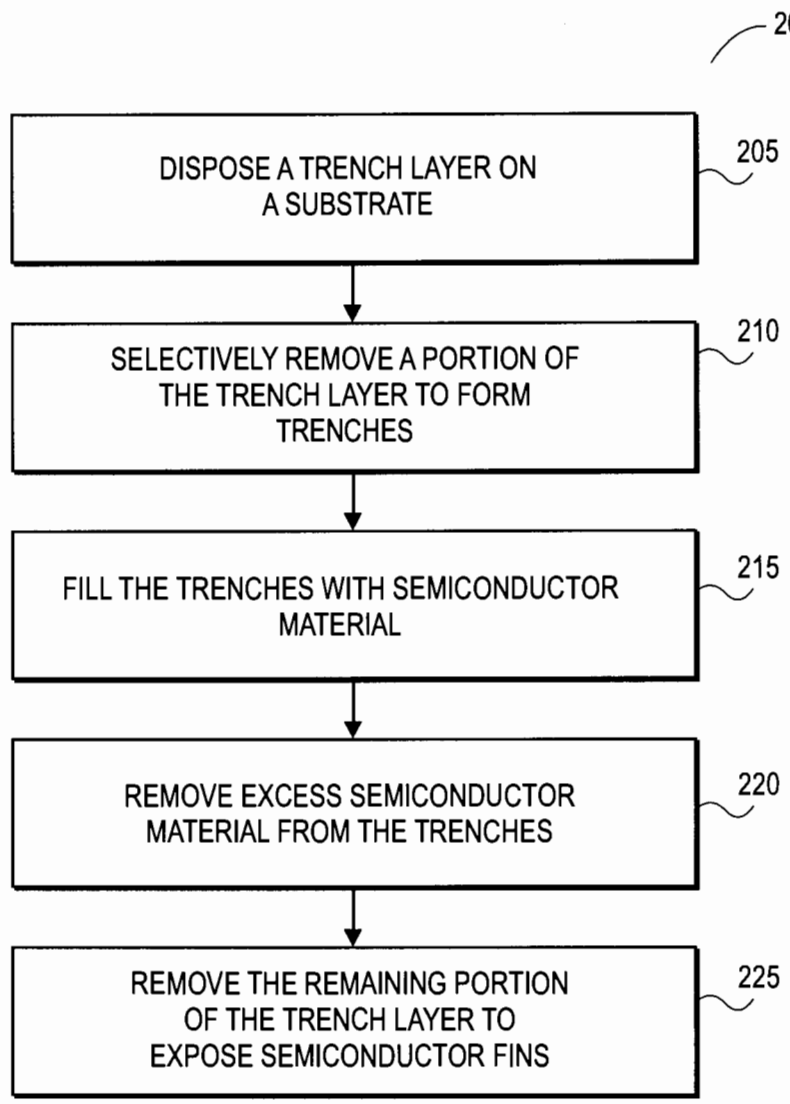

200
DISPOSE A TRENCH LAYER ON A SUBSTRATE
205
SELECTIVELY REMOVE A PORTION OF THE TRENCH LAYER TO FORM TRENCHES
210
FILL THE TRENCHES WITH SEMICONDUCTOR MATERIAL
215
REMOVE EXCESS SEMICONDUCTOR MATERIAL FROM THE TRENCHES
220
REMOVE THE REMAINING PORTION OF THE TRENCH LAYER TO EXPOSE SEMICONDUCTOR FINS
225

FIG. 2

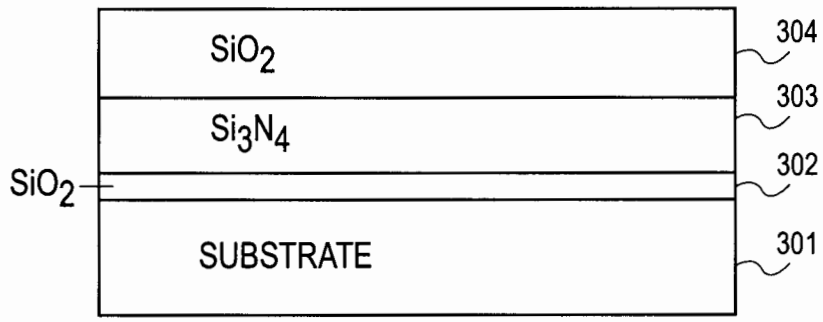


FIG. 3A

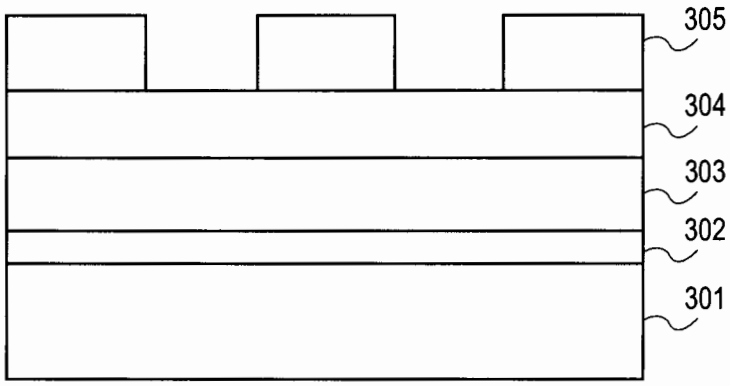


FIG. 3B

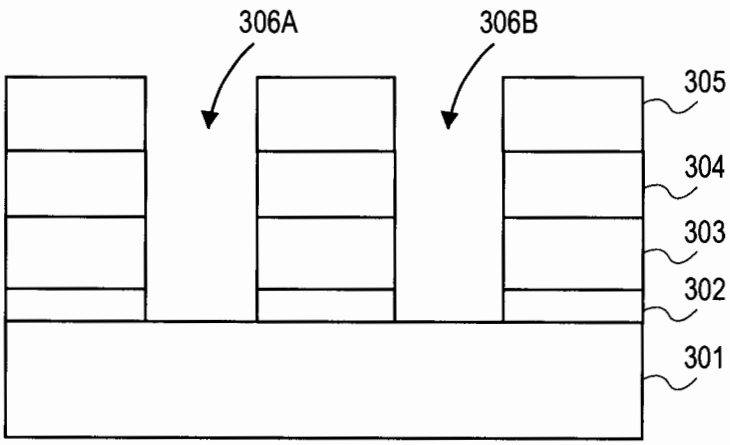


FIG. 3C

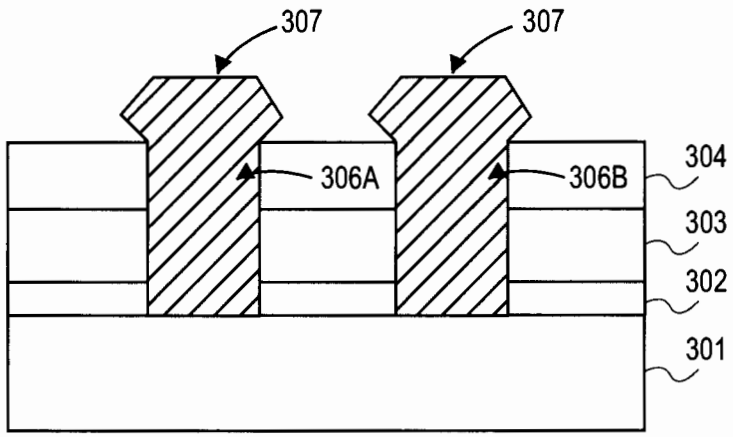


FIG. 3D

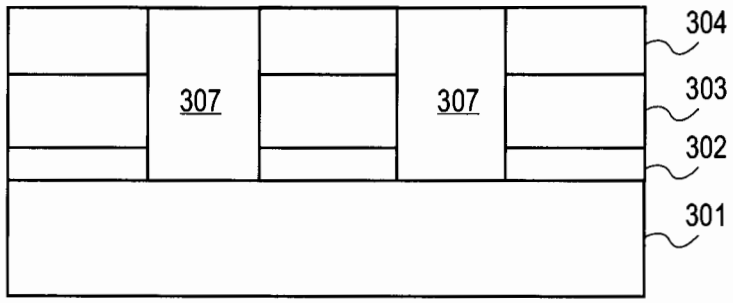


FIG. 3E

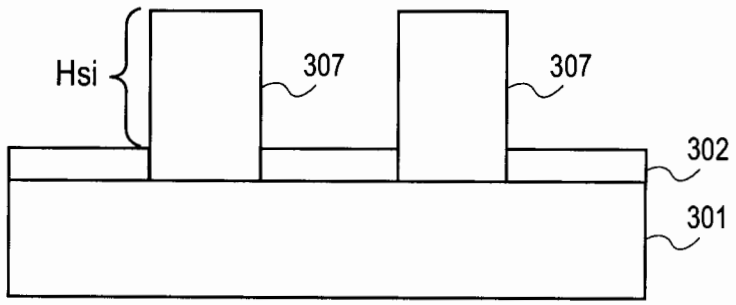


FIG. 3F

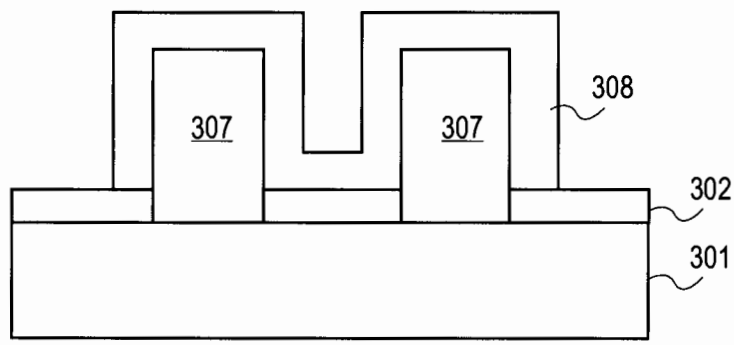


FIG. 3G